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В	PAC PAR	GE 4, PA	ARAGRA ARAGRA PH 5.2 A ARAGRA	APH 5 .DDEI	. 0 CF O "HE	IANGI REIN'	ED VE ' AFT]	ERBIA ER TA	GE A	DDED 2.	"HEI	REIN'	' AFTE	ER TA	ABLE	3.		11/1	19/99
С	RAII • PA LTC QUA • P SPE	OS PER AGE 4, I C IS QM ALIFIEI AGE 6, CIFICA AGE 7,	PARAGI SECONI PARAGR L CERT O CLASS COMBI TION 11 1 K Ω RI	D" TC RAPH IFIED S S M. NED I I PAG ESIST	"LES 6.1 CI AND ANUF FIGUI ES LO	SS THANG HANG THAT ACTU RES 1.2 DNG. DDED	AN OF ED QU FRAD IRING AND 2	R EQU UALIT HAR LINE 2 ON T	AL T TY AS D CA S. TO TI	O 10 R SSURA NDIDA HE SAM	ADS I NCE I ATES ME PA	PER S PROV ARE AGE.	SECON VISION ASSEN THIS I	ID". IS TO MBLI MAK IN CI	STA ED ON ES TH RCUI	TE TH N HE T.		01/1	15/03
D	•	PAGE 3	3, CHAN	GED	INITL	AL RA	TE O	F RAI	S TC	240 R	ADS/S	SEC						03/2	21/05
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G	ADI	DED TE	11, CHAI MPERA	TURE	CYC	LE, C	ONST	ANT A	ACCE	ELERA	ΓΙΟΝ	& RE	EMOVE	ED PI	ND T	EST.			06/09
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	REVISION RECORD	
REV	DESCRIPTION	DATE
L	Changed section 5.8 fr The lead material and finish shall be Kovar with hot solder dip (Finish letter A) in accordance with MIL-PRF-38535 to Lead material and finish shall be gold plating over nickel plating over Kovar	08/08/16
M N	(Finish letter A) in accordance with MIL-PRF-38535 to Lead material and finish shall be	01/04/21 3/19/21

ANALOG DEVICES INC.

1.0 SCOPE:

1.1 This specification defines the performance and test requirements for a microcircuit processed to a space level manufacturing flow.

2.0 APPLICABLE DOCUMENTS:

2.1 <u>Government Specifications and Standards</u>: the following documents listed in the Department of Defense Index of Specifications and Standards, of the issue in effect on the date of solicitation, form a part of this specification to the extent specified herein.

SPECIFICATIONS:

MIL-PRF-38535 Integrated Circuits (Microcircuits) Manufacturing, General Specification for

MIL-STD-883 Test Method and Procedures for Microcircuits

MIL-STD-1835 Microcircuits Case Outlines

2.2 <u>Order of Precedence:</u> In the event of a conflict between the documents referenced herein and the contents of this specification, the order of precedence shall be this specification, MIL-PRF-38535 and other referenced specifications.

3.0 REQUIREMENTS:

- 3.1 <u>General Description</u>: This specification details the requirements for the RH1009 2.5V Reference Dice and Element Evaluation Test Samples, processed to space level manufacturing flow as specified herein.
- 3.2 Part Number: RH1009Dice
- 3.3 Special Handling of Dice: Rad Hard dice require special handling as compared to standard IC dice. Rad Hard dice are susceptible to surface damage due to the absence of silicon nitride passivation that is present on most standard dice. Silicon nitride protects the dice surface from scratches by its hard and dense properties. The passivation on Analog Devices Rad Hard dice is silicon dioxide which is much "softer" than silicon nitride. During the visual and preparation for shipment, ESD safe Tweezers are used and only the edge of the die are touched.

ADI recommends that dice handling be performed with extreme care so as to protect the die surface from scratches. If the need arises to move the die in or out of the chip shipment tray (waffle pack), use an ESD-Safe-Plastic-tipped Bent Metal Vacuum Probe, preferably .020" OD x .010" ID (for use with tiny parts). The wand should be compatible with continuous air vacuums. The tip material should be static dissipative Delrin (or equivalent) plastic.

During die attach, care must be exercised to ensure no tweezers, or other equipment, touch the top of the dice.

3.4 The Absolute Maximum Ratings:

- 3.5 <u>Design, Construction, and Physical Dimensions</u>: Detail design, construction, physical dimensions, and electrical requirements shall be specified herein.
- 3.6 <u>Outline Dimensions and Pad Functions</u>: Dice outline dimensions, pad functions, and locations shall be specified in **Figure 1**.
- 3.7 Radiation Hardness Assurance (RHA):
 - 3.7.1 The manufacturer shall perform a lot sample test as an internal process monitor for total dose radiation tolerance. The sample test is performed with MIL-STD-883 TM1019 Condition A as a guideline.
 - 3.7.2 For guaranteed radiation performance to MIL-STD-883, Method 1019, total dose irradiation, the manufacturer will provide certified RAD testing and report through an independent test laboratory when required as a customer purchase order line item.
 - 3.7.3 Total dose bias circuit is specified in **Figure 2**.
- 3.8 <u>Wafer (or Dice) Probe</u>: Dice shall be 100% probed at Ta = +25°C to the limits shown in **Table I** herein. All reject dice shall be removed from the lot. This testing is normally performed prior to dicing the wafer into chips. Final specifications after assembly are sample tested during the element evaluation.
- 3.9 <u>Wafer Lot Acceptance</u>: Wafer lot acceptance shall be in accordance with MIL-PRF-38535, Appendix A, except for the following: Top side glassivation thickness shall be a **minimum of 4KÅ**.
- 3.10 <u>Wafer Lot Acceptance Report</u>: SEM is performed per MIL-STD-883, Method 2018. Copies of SEM photographs shall be supplied with the Wafer Lot Acceptance Report as part of a Space Data Pack when specified as a customer purchase order line item.
- 3.11 <u>Traceability</u>: Wafer Diffusion Lot and Wafer traceability shall be maintained through Quality Conformance Inspection.
- 4.0 QUALITY CONFORMANCE INSPECTION: Quality Conformance Inspection shall consist of the tests and inspections specified herein.
- 5.0 SAMPLE ELEMENT EVALUATION: A sample from **each wafer supplying dice** shall be assembled and subjected to element evaluation per **Table III** herein.
 - 5.1 <u>100 Percent Visual Inspection</u>: All dice supplied to this specification shall be inspected in accordance with MIL-STD-883, Method 2010, Condition A. All reject dice shall be removed from the lot.
 - 5.2 <u>Electrical Performance Characteristics for Element Evaluation</u>: The electrical performance characteristics shall be as specified in **Table I** and **Table II** herein.
 - 5.3 <u>Sample Testing</u>: Each wafer supplying dice for delivery to this specification shall be subjected to element evaluation sample testing. No dice shall be delivered until all the lot sample testing has been performed and the results found to be acceptable unless the customer supplies a written approval for shipment prior to completion of wafer qualification as specified in this specification.

- 5.4 Part Marking of Element Evaluation Sample Includes:
 - 5.4.1 LTC Logo
 - 5.4.2 LTC Part Number
 - 5.4.3 Date Code
 - 5.4.4 Serial Number
 - 5.4.5 ESD Identifier per MIL-PRF-38535, Appendix A
 - 5.4.6 Diffusion Lot Number
 - 5.4.7 Wafer Number
- 5.5 Burn-In Requirement: Burn-In circuit for TO46 package is specified in **Figure 3**.
- 5.6 <u>Mechanical/Packaging Requirements</u>: Case Outline and Dimensions are in accordance with **Figure 4.**
- 5.7 Terminal Connections: The terminal connections shall be as specified in **Figure 5**.
- 5.8 <u>Lead Material and Finish:</u> Shall be gold plating over nickel plating over Kovar.
- 6.0 VERIFICATION (QUALITY ASSURANCE PROVISIONS)
 - 6.1 <u>Quality Assurance Provisions</u>: Quality Assurance provisions shall be in accordance with MIL-PRF-38535. Analog Devices is a QML certified company and all Rad Hard candidates are assembled on qualified Class S manufacturing lines.
 - 6.2 Sampling and Inspection: Sampling and Inspection shall be in accordance with **Table III** herein.
 - 6.3 Screening: Screening requirements shall be in accordance with **Table III** herein.
 - 6.4 Deliverable Data: Deliverable data that will ship with devices when a Space Data Pack is ordered:
 - 6.4.1 Lot Serial Number Sheets identifying all Canned Sample devices accepted through final inspection by serial number.
 - 6.4.2 100% attributes (completed element evaluation traveler).
 - 6.4.3 Element Evaluation variables data, including Burn-In and Op Life
 - 6.4.4 SEM photographs (3.10 herein)
 - 6.4.5 Wafer Lot Acceptance Report (3.9 herein)
 - 6.4.6 A copy of outside test laboratory radiation report if ordered
 - 6.4.7 Certificate of Conformance certifying that the devices meet all the requirements of this specification and have successfully completed the mandatory tests and inspections herein.

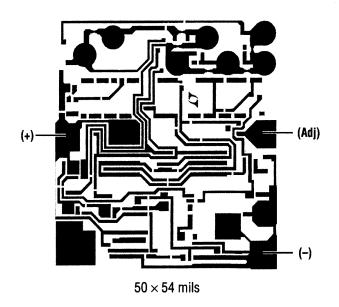
ANALOG DEVICES INC.

Note: Items 6.4.1 and 6.4.7 will be delivered as a minimum, with each shipment.

7.0 <u>Packaging Requirements</u>: Packaging shall be in accordance with Appendix A of MIL-PRF-38535. All dice shall be packaged in multicavity containers composed of conductive, anti-static, or static dissipative material with an external conductive field shielding barrier.

DICE OUTLINE DIMENSIONS AND PAD FUNCTIONS

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Backside (substrate) is an alloyed gold layer. Connect backside to (-) pin. Back Lap = 12mils

DIE CROSS REFERENCE

LTC Finished	Order DICE CANDIDATE
Part Number	Part Number Below
RH1009	RH1009 DICE

PAD FUNCTION

1. (+)

2. (Adj)

3. (–)

FIGURE 1

TOTAL DOSE BIAS CIRCUIT

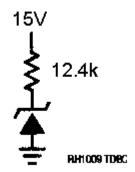
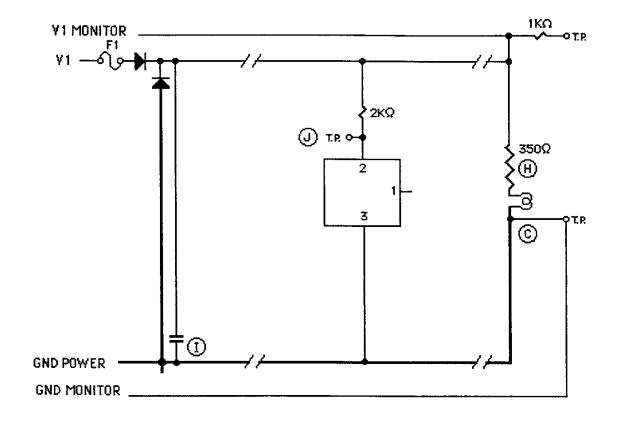


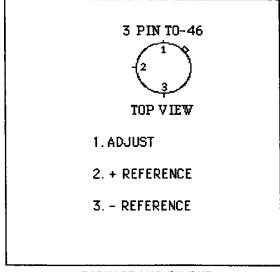
FIGURE 2

BURN-IN CIRCUIT



NOTES:

- 1. Unless otherwise specified, component tolerances shall be per military specification. 2. Tj = 169 $^{\circ}$ C maximum.
- 3. $Ta = 150 \, ^{\circ}C$.
- 4. Burn-in Voltages: Y1 = +20Y to +22Y

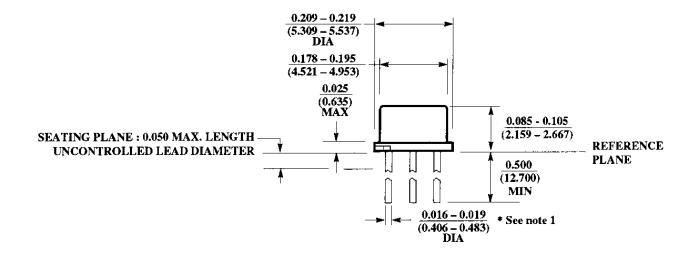


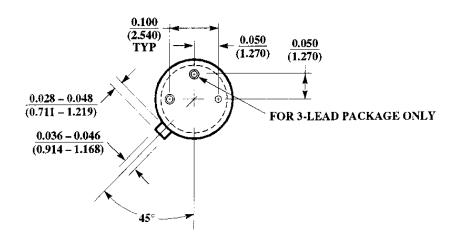
PACKAGE AND PINOUT

FIGURE 3

TO46, 3 LEADS, CASE OUTLINE

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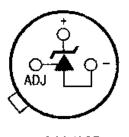
NOTE: 1. FOR SOLDER DIP LEAD FINISH, LEAD DIAMETER IS $\frac{0.016-0.024}{(0.406-0.610)}$

FIGURE 4

 θ ja = +440°C/W θ jc = +80°C/W

TERMINAL CONNECTIONS

BOTTOM VIEW



H PACKAGE 3-LEAD TO-46 METAL CAN

FIGURE 5

<u>TABLE I DICE ELECTRICAL CHARACTERISTICS – (Preirradiation) Element Evaluation (Notes 2 and 3)</u>

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				TJ	= 25°C	SUB-	
SYMBOL	PARAMETER	CONDITIONS	NOTES	MIN	TYP MAX	GROUP	UNITS
$\overline{V_Z}$	Reverse Breakdown Voltage	T _A = 25°C, I _R = 1mA		2.495	2.505	1	V
$\frac{\Delta V_Z}{\Delta I_R}$	Reverse Breakdown Change with Current	$T_A = 25^{\circ}C, 400\mu A \le I_R \le 10mA$			6	1	mV
r _Z	Reverse Dynamic Impedance	T _A = 25°C, I _R = 1mA (Note 1)	1		0.6		Ω

Note 1: Guaranteed by correlation but not tested.

Note 2: Dice are probe tested at 25°C to the limits above. Final specifications after assembly cannot be guaranteed at the die level due to yield loss and assembly shifts. For absolute maximum ratings, typical

specifications, performance curves and finished product specifications, please refer to the standard product data sheet.

Note 3: For dice tested to tighter limits than those listed above and/or lot qualification based on sample lot assembly and testing, please contact LTC Marketing.

TABLE II ELECTRICAL CHARACTERISTICS – Post-Irradiation (Note 2)

				10KR	AD(Si)	20KR	AD(Si)	50KR	AD(Si)	100KF	AD(Si)	200KF	RAD(Si)	
SYMBOL	PARAMETER	CONDITIONS	NOTES	MIN	MAX	UNITS								
VZ	Reverse Breakdown Voltage	I _R = 1mA		2.495	2.505	2.495	2.505	2.495	2.505	2.495	2.505	2.495	2.505	V
$\frac{\Delta V_Z}{\Delta I_Z}$	Reverse Breakdown Voltage Change with Current	400μA ≤ I _R ≤ 10mA			6		6		8		10		12	m۷
r _Z	Reverse Dynamic Impedance	I _R = 1mA	1		0.6		0.6		8.0		1.0		1.4	Ω

Note 1: Guaranteed by design, characterization or correlation to other tested parameters.

Note 2: $T_A = 25$ °C unless otherwise noted.

TABLE III RH ELEMENT EVALUATION TABLE QUALIFICATION OF DICE SALES



RH CANNED SAMPLE TABLE FOR QUALIFYING DICE SALES

			RH CANNED SAMPLE TABLE FOR QUALIFY	ING DICE SALES	0,	
	CLAS	S		MIL-S	TD-883	QUANTITY
K/S	٧	Н/В	OPERATION	METHOD	CONDITION	(ACCEPT NUMBER)
×	×		SEM	2018	N/A	REF. METHOD 2018 FOR S/S
×	×	X	ELEMENT ELECTRICAL (WAFER SORT @ 25°C)			100%
×	×	×		2010	А	100%
×	×	×		2010	А	ASSEMBLED PARTS ONLY
×	×		DIE SHEAR MONITOR	2019		
×	×		BOND PULL MONITOR	2011		
×	×		STABILIZATION BAKE	1008	С	ASSEMBLED PARTS ONLY
×	×		TEMPERATURE CYCLE	1010	С	
×	×		CONSTANT ACCELERATION	2001	E	
×	×		FINE LEAK	1014	А	
×	×		GROSS LEAK	1014	С	
×	×		FIRST ROOM ELECTRICAL - READ & RECORD			45(0)
Τ	T		(REPLACE ANY ASSEMBLY-RELATED REJECTS)			
×	×		PRE BURN-IN ELECT. READ & RECORD @ +125°C or +150°C, -55°C			
×	×		BURN-IN: +125°C/240 hrs. or +150°C/120 hrs.	1015	+ 125°c MINIMUM 240 HOURS	
×	×		POST BURN-IN ELECT. READ & RECORD @ 25°C			
×	×		POST BURN-IN ELECT. READ & RECORD @ +125°C or +150°C, -55°C			
	×		TOTAL IRRADIATION DOSE	1019	Α	
×	×		PRE OP-LIFE ELECTRICAL @ 25°C READ & RECORD			
×	×		OPERATING LIFE: +125°C/1000 hrs. or +150°C/500 hrs.	1005	+ 125°c MINIMUM 1000 HOURS	
×	×		POST OP-LIFE ELECT. (R & R @ 25°C, +125°C OR +150°C, -55°C			
X	X	X	WIRE BOND EVALUATION	2011		15(0) OR 25(1) - # of wires
LTC	is no	ot qu	ualified to process to MIL-PRF-38534. This is an LTC imposed eler	ment evaluation	n that follows	
\leq	-STD	-88	3 test methods and conditions. Please note the quantity and acc	ept number fro	m Sample Size Se	ries of
5%	, acc	ept	on 0, and note that the actual sample and accept number does i	not begin until	Subgroup 6 OP-LI	FE.
Test	ts wi	thin	Subgroup 5 may be performed in any sequence.			
LTC	's rac	diati	on tolerance (RH) die has a topside glassivation thickness of 4KA	minimum.		
Sam to a	nple :	sizes nmo	s on the travelers may be larger than that indicated in the above idate extra units for replacement devices in the event of equipm	table; however	r, the larger samp	ile size is iembly
rela kep	ted ı t seg	rejec ţrega	ts in Subgroup 6, and for Wire Bond Evaluation, Surgroup 7. The sted and, if used for qualification, has all the required processing	larger sample imposed.	size is at all times	
	SUBGROUP K/S 1					CLASS K/S V H/B SEM COPERATION X X SELEMENT ELECTRICAL (WAFER SORT @ 25°C) X X SELEMENT VISUAL (2nd OP) X X NITERNAL VISUAL (3nd OP) X X NITERNAL VISUAL (3nd OP) X X SINTERNAL VISUAL (3nd OP) X X DIE SHEAR MONITOR X X DIE SHEAR MONITOR X X FIRBITATION BAKE X X PESTEUR-NHIBLECT. FEAD & RECORD @ +129°C - +150°C599°C X X PESTEUR-NHIBLECT. FEAD & RECORD @ -129°C - +150°C599°C X X PESTEUR-NHIBLECT. FEAD & RECORD @ -129°C - +150°C599°C X X PESTEUR-NHIBLECT. FEAD & RECORD @ -129°C - +150°C599°C X X PESTEUR-NHIBLECT. FEAD & RECORD @ -129°C - +150°C599°C X X PESTEUR-NHIBLECT. FEAD & RECORD @ -129°C - +150°C599°C X X PESTEUR-NHIBLECT. FEAD & RECORD @ -129°C - +150°C599°C X X PESTEUR-NHIBLECT. FEAD & RECORD @ -129°C - +150°C599°C X X V POSTEUR-NHIBLECT. FEAD & RECORD @ -129°C - +150°C599°C X X V POSTEUR-NHIBLECT. FEAD & RECORD @ -129°C - +150°C599°C X X V POSTEUR-NHIBLECT. FEAD & RECORD @ -129°C - +150°C599°C X X V POSTEUR-NHIBLECT. FEAD & RECORD @ -129°C - +150°C599°C X X V POSTEUR-NHIBLECT. FEAD & RECORD @ -129°C - +150°C599°C X X V POSTEUR-NHIBLECT. FEAD & RECORD @ -129°C - +150°C599°C X X V POSTEUR-NHIBLECT. FEAD & RECORD @ -129°C - +150°C599°C X X V POSTEUR-NHIBLECT. FEAD & RECORD @ -129°C - +150°C599°C X X V POSTEUR-NHIBLECT. FEAD & RECORD @ -129°C - +150°C599°C X X V POSTEUR-NHIBLECT. FEAD & RECORD @ -129°C - +150°C599°C X X V POSTEUR-NHIBLECT. FEAD & RECORD @ -129°C - +150°C599°C X X V POSTEUR-NHIBLECT. FEAD & RECORD @ -129°C - +15